

View Online at <https://aerobasegroup.com/nsn/5980-01-460-5633>

General Description:

Gallium-arsenide light emitting diode; silicon npn darlington phototransistor per channel; one channel in a 4-pin dip package; 35.0 volts breakdown voltage; 150.0 milliwatts power dissipation; 50.0 milliamps forward current; storage temperature range minus 55.0 degrees c to plus 125.0 degrees c

Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

Yes - demil/mli

Fig:

A23900